Dual buffer/line driver; 3-state

Rev. 7 — 6 May 2013

Product data sheet

1. General description

The 74AHC2G126 and 74AHCT2G126 are high-speed Si-gate CMOS devices. They provide a dual non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (nOE). A LOW at nOE causes the output to assume a high-impedance OFF-state.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

2. Features and benefits

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - ◆ HBM JESD22-A114E: exceeds 2000 V
 - MM JESD22-A115-A: exceeds 200 V
 - CDM JESD22-C101C: exceeds 1000 V
- Specified from –40 °C to +125 °C

3. Ordering information

Table 1.Ordering information

Type number	Package	Package									
	Temperature range	Name	Description	Version							
74AHC2G126DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads;	SOT505-2							
74AHCT2G126DP			body width 3 mm; lead length 0.5 mm								
74AHC2G126DC	–40 °C to +125 °C	VSSOP8	VSSOP8 plastic very thin shrink small outline package;								
74AHCT2G126DC			8 leads; body width 2.3 mm								
74AHC2G126GD	–40 °C to +125 °C	XSON8									
74AHCT2G126GD			leads; 8 terminals; body $3 \times 2 \times 0.5$ mm								



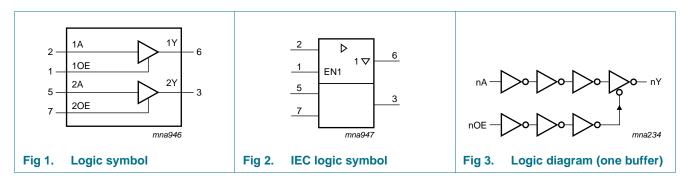
Dual buffer/line driver; 3-state

4. Marking

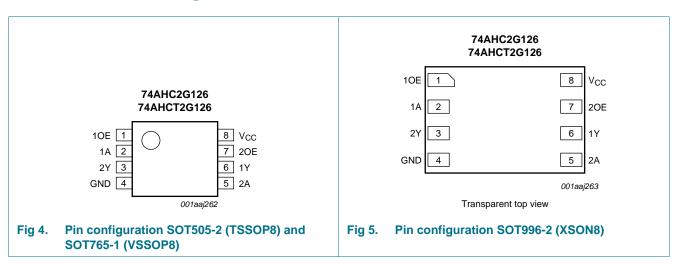
Table 2. Marking codes	
Type number	Marking ^[1]
74AHC2G126DP	A26
74AHCT2G126DP	C26
74AHC2G126DC	A26
74AHCT2G126DC	C26
74AHC2G126GD	A26
74AHCT2G126GD	C26

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information



6.1 Pinning

Dual buffer/line driver; 3-state

6.2 Pin description

Table 3. Pin c	lescription	
Symbol	Pin	Description
10E, 20E	1, 7	output enable input (active HIGH)
1A, 2A	2, 5	data input
GND	4	ground (0 V)
1Y, 2Y	6, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table ^[1]		
Control	Input	Output
nOE	nA	nY
Н	L	L
Н	Н	Н
L	Х	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V	<u>[1]</u> –20	-	mA
I _{OK}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	75	mA
I _{GND}	ground current		-75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K. For XSON8 package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

Dual buffer/line driver; 3-state

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74	74AHC2G126			74AHCT2G126		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	V_{CC} = 3.3 V \pm 0.3 V	-	-	100	-	-	-	ns/V
	and fall rate	$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C	to +85 °C	_40 °C	to +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHC2	G126	'				•				•
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level	$V_I = V_{IH} \text{ or } V_{IL}$								
	output voltage	I_{O} = –50 $\mu\text{A};V_{CC}$ = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_{O} = -50 μ A; V_{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I_{O} = –50 $\mu\text{A};V_{CC}$ = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		I_{O} = -8.0 mA; V_{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level	$V_I = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_0 = 50 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 50 \ \mu A; \ V_{CC} = 3.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 50 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I_{O} = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I _{OZ}	OFF-state output current	$V_I = V_{CC} \text{ or GND};$ $V_{CC} = 5.5 \text{ V}$	-	-	0.25	-	2.5	-	10	μΑ
lı	input leakage current	$V_I = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current		-	-	1.0	-	10	-	40	μΑ

74AHC_AHCT2G126

Dual buffer/line driver; 3-state

Symbol	Parameter	Conditions		25 °C		–40 °C	to +85 °C	–40 °C	to +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
CI	input capacitance		-	1.5	10	-	10	-	10	pF
74AHCT	2G126									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{он}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
l _{oz}	OFF-state output current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	0.25	-	2.5	-	10	μA
lı	input leakage current	$V_I = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μA
СС	supply current		-	-	1.0	-	10	-	40	μA
VI _{CC}	additional supply current	per input pin; $V_I = 3.4 V$; other inputs at V_{CC} or GND; $I_O = 0 A$; $V_{CC} = 5.5 V$	-	-	1.35	-	1.5	-	1.5	mA
Cı	input capacitance		-	1.5	10	-	10	-	10	pF

Table 7. Static characteristics ... continued Voltages are referenced to GND (ground = 0.)

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; for test circuit see <u>Figure 8</u>.

Symbol	Parameter	Conditions			25 °C		–40 °C	to +85 °C	–40 °C to +125 °C		Unit
				Min	Тур	Мах	Min	Max	Min	Max	
74AHC2	G126										
t _{pd} propagation delay	propagation	nA to nY; see Figure 6	<u>[1]</u>								
	V_{CC} = 3.0 V to 3.6 V	[2]									
		C _L = 15 pF		-	4.7	8.0	1.0	9.5	1.0	11.5	ns
		C _L = 50 pF		-	6.6	11.5	1.0	13.0	1.0	14.5	ns
		V_{CC} = 4.5 V to 5.5 V	[3]								
	C _L = 15 pF		-	3.4	5.5	1.0	6.5	1.0	7.0	ns	
		C _L = 50 pF		-	4.8	7.5	1.0	8.5	1.0	9.5	ns

Dual buffer/line driver; 3-state

Symbol	Parameter	Conditions			25 °C		–40 °C	to +85 °C	–40 °C to +125 °C		Uni
				Min	Тур	Max	Min	Max	Min	Max	
en	enable time	nOE to nY; see Figure 7	[1]								
		V_{CC} = 3.0 V to 3.6 V	[2]								
		C _L = 15 pF		-	5.0	8.0	1.0	9.5	1.0	11.5	ns
		C _L = 50 pF		-	6.9	11.5	1.0	13.0	1.0	14.5	ns
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C _L = 15 pF		-	3.6	5.1	1.0	6.0	1.0	6.5	ns
		C _L = 50 pF		-	4.9	7.5	1.0	9.0	1.0	9.5	ns
dis	disable time	nOE to nY; see Figure 7	[1]								
		V_{CC} = 3.0 V to 3.6 V	[2]								
		C _L = 15 pF		-	6.0	9.7	1.0	11.5	1.0	12.5	ns
		C _L = 50 pF		-	8.3	13.2	1.0	15.0	1.0	16.5	ns
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C _L = 15 pF		-	4.1	6.8	1.0	8.0	1.0	8.5	ns
		C _L = 50 pF		-	5.7	8.8	1.0	10.0	1.0	11.0	ns
C _{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}; f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	10	-	-	-	-	-	pF
74AHCT	2G126										
pd	propagation	nA to nY; see Figure 6	[1]								
	delay	V_{CC} = 4.5 V to 5.5 V	[3]								
		C _L = 15 pF		-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF		-	4.8	7.5	1.0	8.5	1.0	9.5	ns
en	enable time	nOE to nY; see Figure 7	[1]								
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C _L = 15 pF		-	3.9	5.1	1.0	6.0	1.0	6.5	ns
		C _L = 50 pF		-	5.1	7.5	1.0	9.0	1.0	9.5	ns
dis	disable time	nOE to nY; see Figure 7	[1]								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C _L = 15 pF		-	4.5	6.8	1.0	8.0	1.0	8.5	ns
		$C_1 = 50 \text{pF}$		-	6.1	8.8	1.0	10.0	1.0	11.0	ns

Table 8.Dynamic characteristics ... continuedGND = 0.V: for test circuit see Figure 8

Dual buffer/line driver; 3-state

Symbol	ymbol Parameter Conditions		25 °C		–40 °C to +85 °C		–40 °C to +125 °C		Uni		
				Min	Тур	Max	Min	Max	Min	Max	
C _{PD}	•	per buffer; $C_L = 50 \text{ pF}; f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	[4]	-	10	-	-	-	-	-	pF

Table 8. Dynamic characteristics ... continued

 t_{dis} is the same as t_{PLZ} and t_{PHZ} .

[2] Typical values are measured at V_{CC} = 3.3 V.

- [3] Typical values are measured at $V_{CC} = 5.0$ V.
- [4] C_{PD} is used to determine the dynamic power dissipation P_D (μ W).

 $\mathsf{P}_{\mathsf{D}} = \mathsf{C}_{\mathsf{P}\mathsf{D}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}{}^2 \times \mathsf{f}_i + \sum \left(\mathsf{C}_{\mathsf{L}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}{}^2 \times \mathsf{f}_o\right)$ where:

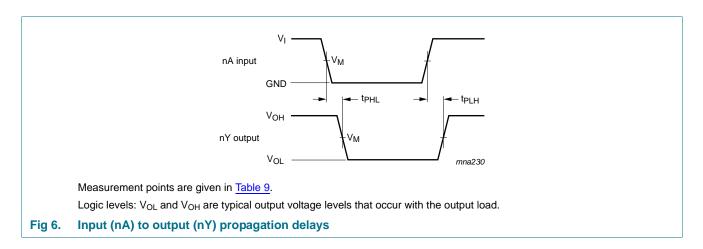
 $f_i = input frequency in MHz;$

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts.

12. Waveforms



Dual buffer/line driver; 3-state

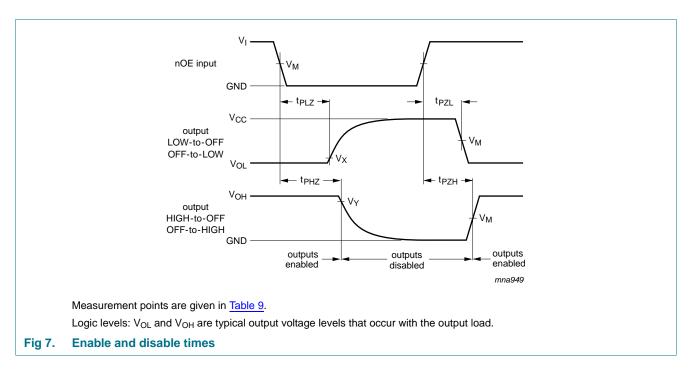


Table 9.Measurement points

Туре	Input	Output					
	V _M	V _M	V _X	V _Y			
74AHC2G126	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.3 V	V _{OH} – 0.3 V			
74AHCT2G126	1.5 V	0.5V _{CC}	V _{OL} + 0.3 V	V _{OH} – 0.3 V			

NXP Semiconductors

74AHC2G126; 74AHCT2G126

Dual buffer/line driver; 3-state

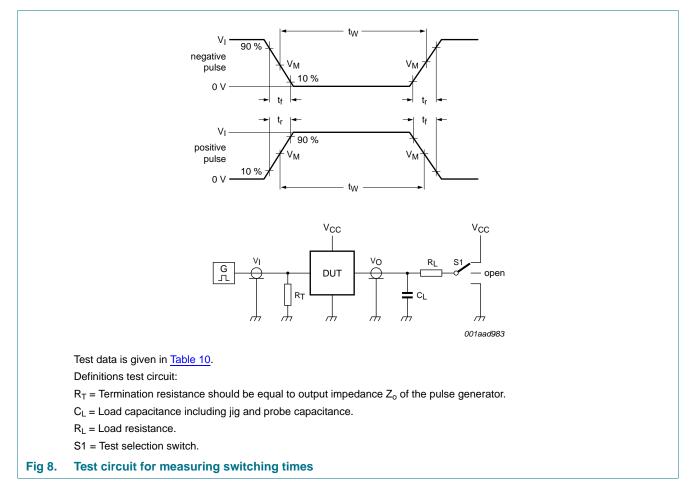


Table 10. Test data

Туре	Input		Load		S1 position		
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
74AHC2G126	V _{CC}	\leq 3 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}
74AHCT2G126	3 V	\leq 3 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}

Dual buffer/line driver; 3-state

13. Package outline

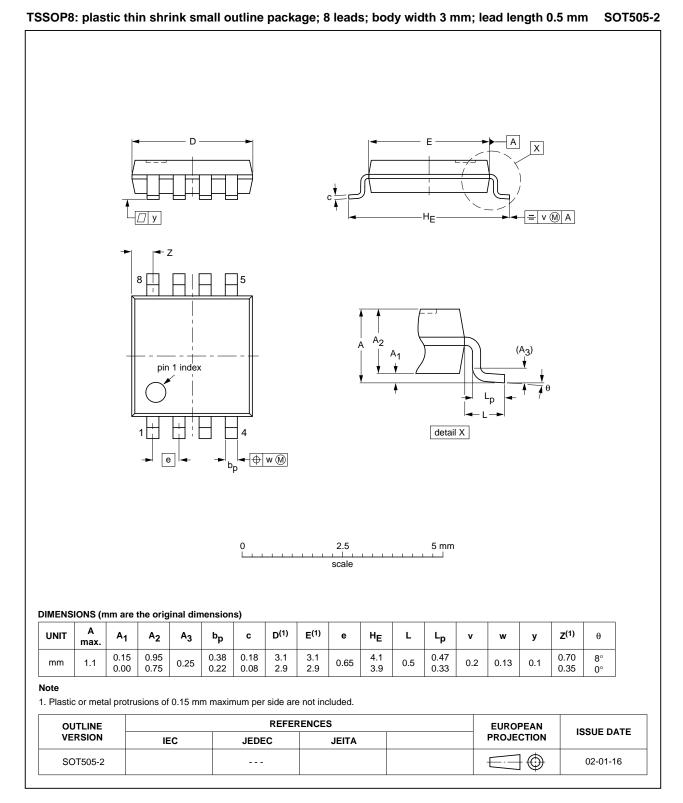


Fig 9. Package outline SOT505-2 (TSSOP8)

All information provided in this document is subject to legal disclaimers.

74AHC_AHCT2G126

Dual buffer/line driver; 3-state

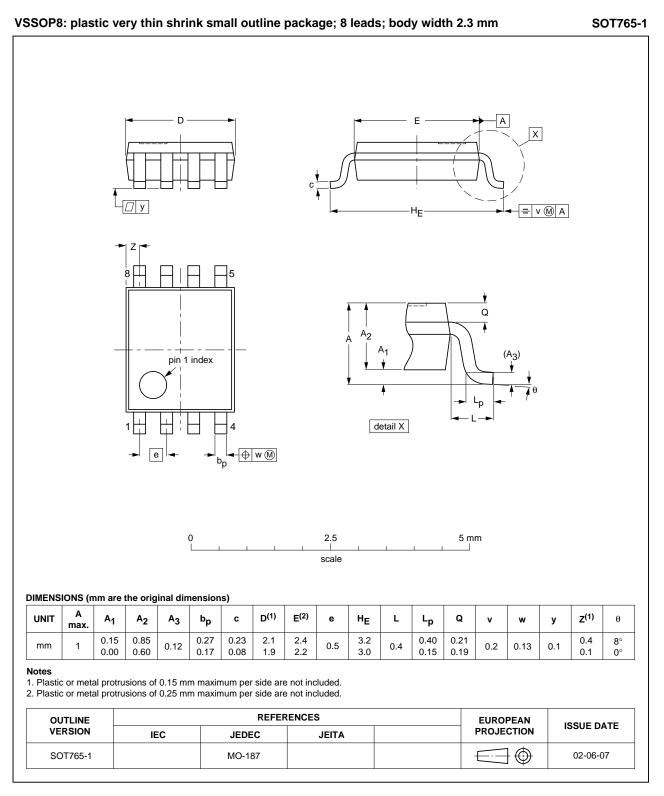
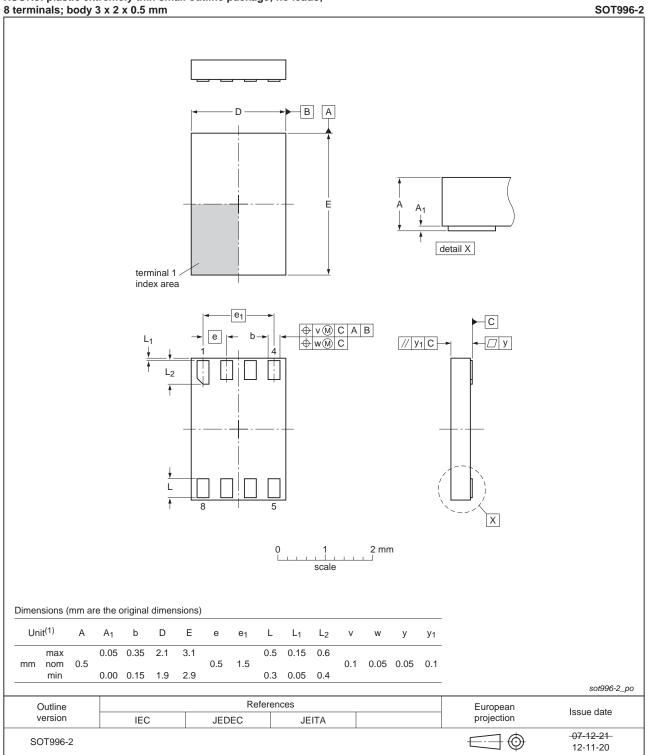


Fig 10. Package outline SOT765-1 (VSSOP8)

74AHC_AHCT2G126
Product data sheet

11 of 16

Dual buffer/line driver; 3-state



XSON8: plastic extremely thin small outline package; no leads;

Fig 11. Package outline SOT996-2 (XSON8)

All information provided in this document is subject to legal disclaimers.

74AHC_AHCT2G126

Dual buffer/line driver; 3-state

14. Abbreviations

AcronymDescriptionCMOSComplementary Metal Oxide SemiconductorCDMCharged Device ModelDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelTTLTransistor-Transistor Logic	Table 11. Abbreviations		
CDMCharged Device ModelDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine Model	Acronym	Description	
DUT Device Under Test ESD ElectroStatic Discharge HBM Human Body Model MM Machine Model	CMOS	Complementary Metal Oxide Semiconductor	
ESD ElectroStatic Discharge HBM Human Body Model MM Machine Model	CDM	Charged Device Model	
HBM Human Body Model MM Machine Model	DUT	Device Under Test	
MM Machine Model	ESD	ElectroStatic Discharge	
	HBM	Human Body Model	
TTL Transistor-Transistor Logic	MM	Machine Model	
5	TTL	Transistor-Transistor Logic	

15. Revision history

Table 12. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT2G126 v.7	20130506	Product data sheet	-	74AHC_AHCT2G126 v.6
Modifications:	 For type nun XSON8. 	nber 74AHC2G126GD and	d 74AHCT2G126GE	OXSON8U has changed to
74AHC_AHCT2G126 v.6	20111108	Product data sheet	-	74AHC_AHCT2G126 v.5
Modifications:	 Legal pages 	updated.		
74AHC_AHCT2G126 v.5	20110324	Product data sheet	-	74AHC_AHCT2G126 v.4
74AHC_AHCT2G126 v.4	20090427	Product data sheet	-	74AHC_AHCT2G126 v.3
74AHC_AHCT2G126 v.3	20090115	Product data sheet	-	74AHC_AHCT2G126 v.2
74AHC_AHCT2G126 v.2	20040921	Product data sheet	-	74AHC_AHCT2G126 v.1
74AHC_AHCT2G126 v.1	20040113	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

16.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

16.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Dual buffer/line driver; 3-state

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond

NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

17. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

Dual buffer/line driver; 3-state

18. Contents

1	General description 1
2	Features and benefits 1
3	Ordering information 1
4	Marking 2
5	Functional diagram 2
6	Pinning information 2
6.1	Pinning 2
6.2	Pin description 3
7	Functional description 3
8	Limiting values 3
9	Recommended operating conditions 4
10	Static characteristics 4
11	Dynamic characteristics 5
12	Waveforms
13	Package outline 10
14	Abbreviations 13
15	Revision history 13
16	Legal information 14
16.1	Data sheet status 14
16.2	Definitions 14
16.3	Disclaimers
16.4	Trademarks 15
17	Contact information 15
18	Contents 16

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2013.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 6 May 2013 Document identifier: 74AHC_AHCT2G126

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

NXP:

74AHC2G126DC,125 74AHC2G126DP,125 74AHC2G126GD,125